# NUP1105LT1G, SZNUP1105LT1G

# **ESD Protection Diode**

# Single Line CAN/LIN Bus Protector

The NUP1105L has been designed to protect LIN and single line CAN transceivers from ESD and other harmful transient voltage events. This device provides bidirectional protection for the data line with a single SOT-23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

#### **Features**

- SOT-23 Package Allows One Separate Bidirectional Configuration
- 350 W Peak Power Dissipation per Line (8 x 20 usec Waveform)
- Low Reverse Leakage Current (< 100 nA)
- IEC Compatibility: IEC 61000-4-2 (ESD): Level 4
  - IEC 61000-4-4 (EFT): 40 A 5/50 ns
  - IEC 61000-4-5 (Lighting) 8.0 A (8/20 μs)
- ISO 7637-1, Nonrepetitive EMI Surge Pulse TBD
- ISO 7637–3, Repetitive Electrical Fast Transient (EFT) TBD EMI Surge Pulses
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **Applications**

- Automotive Electronics
  - LIN Bus
  - ◆ Single Line CAN
- Industrial Control Networks
  - Smart Distribution Systems (SDS<sup>®</sup>)
  - ◆ DeviceNet<sup>TM</sup>



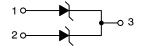
## ON Semiconductor®

www.onsemi.com

# SOT-23 BIDIRECTIONAL VOLTAGE SUPPRESSOR 350 W PEAK POWER



SOT-23 CASE 318 STYLE 27



PIN 1. ANODE 2. ANODE

3. CATHODE

### **MARKING DIAGRAM**



27H = Device Code
M = Date Code
• = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NUP1105LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZNUP1105LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NUP1105LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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## MAXIMUM RATINGS (T<sub>J</sub> = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation 8 x 20 μs Double Exponential Waveform (Note 1)	350	W
TJ	Operating Junction Temperature Range	-55 to 150	°C
T <sub>J</sub>	Storage Temperature Range	-55 to 150	°C
TL	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body model (HBM) Machine Model (MM) IEC 61000-4-2 Specification (Contact)	16 400 30	kV V kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V <sub>RWM</sub>	Reverse Working Voltage	(Note 2)	24			V
V <sub>BR</sub>	Breakdown Voltage	I <sub>T</sub> = 1 mA (Note 3)	25.7		28.4	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> = 24 V		15	100	nA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 5 A (8 x 20 μs Waveform) (Note 4)			40	V
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 8 A (8 x 20 μs Waveform) (Note 4)			44	V
I <sub>PP</sub>	Maximum Peak Pulse Current	8 x 20 μs Waveform (Note 4)			8.0	Α
CJ	Capacitance	$V_R = 0$ V, f = 1 MHz (Anode to GND) $V_R = 0$ V, f = 1 MHz (Anode to Anode)			60 30	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse waveform per Figure 1.
   Include SZ-prefix devices where applicable.

<sup>1.</sup> Non-repetitive current pulse per Figure 1.

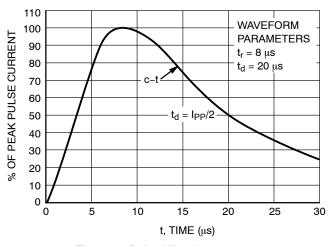
<sup>2.</sup> Surge protection devices are normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal or greater than the DC or continuous peak operating voltage level.

3. V<sub>BR</sub> is measured at pulse test current I<sub>T</sub>.

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## **TYPICAL PERFORMANCE CURVES**

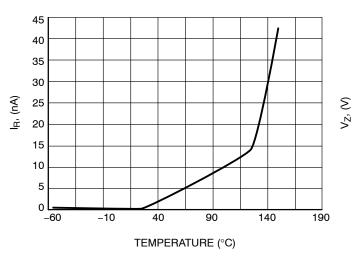
 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 



12.0 € PULSE WAVEFORM IPP, PEAK PULSE CURRENT 8 x 20 μs per Figure 1 10.0 8.0 6.0 4.0 2.0 0.0 30 35 40 25 45 50 V<sub>C</sub>, CLAMPING VOLTAGE (V)

Figure 1. Pulse Waveform, 8  $\times$  20  $\mu s$ 

Figure 2. Clamping Voltage vs Peak Pulse Current



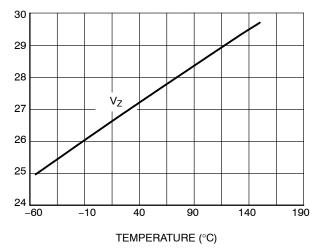


Figure 3. Typical Leakage vs. Temperature

Figure 4. Typical  $V_Z @ 1.0 \ \text{mA} \ \text{vs.}$  Temperature

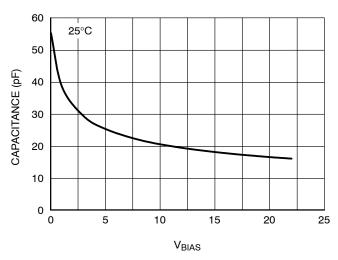


Figure 5. Capacitance vs.  $V_{\text{BIAS}}$ 

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### **APPLICATIONS SECTION**

The NUP1105L provides a surge protection solution for the LIN data communication bus. The NUP1105L is a dual bidirectional surge protection device in a compact SOT-23 package. This device is based on Zener technology that optimizes the active area of a PN junction to provide robust protection against transient EMI surge voltage and ESD. The NUP1105L has been tested to EMI and ESD levels that exceed the specifications of popular high speed LIN networks.

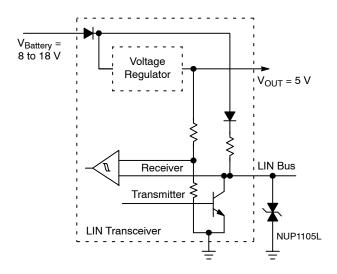


Figure 6. LIN Transceiver

The NUP1105L device can be used to provide transcient voltage suppression for a single data line CAN system. Figure 7 provides an example of a single data line CAN protection circuit.

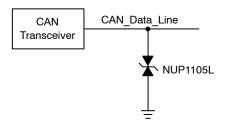


Figure 7. High-Speed and Fault Tolerant CAN Surge Protection Circuit



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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